

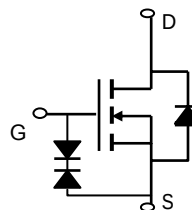
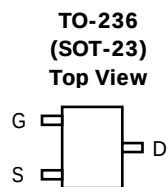
AO3434
N-Channel Enhancement Mode Field Effect Transistor

General Description

The AO3434 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. It is ESD protected. *Standard Product AO3434 is Pb-free (meets ROHS & Sony 259 specifications).*

Features

$V_{DS} (V) = 30V$
 $I_D = 4.2A$ ($V_{GS} = 10V$)
 $R_{DS(ON)} < 52m\Omega$ ($V_{GS} = 10V$)
 $R_{DS(ON)} < 75m\Omega$ ($V_{GS} = 4.5V$)


ESD Protected

Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter		Symbol	Maximum		Units
			10 sec	Steady-State	
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	±20		V
Continuous Drain Current ^{A,F}	T _A =25°C	I _D	4.2	3.5	A
	T _A =70°C		3.3	2.8	
Pulsed Drain Current ^B		I _{DM}	30		
Power Dissipation	T _A =25°C	P _D	1.4	1.0	W
	T _A =70°C		0.9	0.64	
Junction and Storage Temperature Range		T _J , T _{STG}	-55 to 150		°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10s$	$R_{\theta JA}$	70	90	$^\circ C/W$
Maximum Junction-to-Ambient ^A	Steady-State		100	125	$^\circ C/W$
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	63	80	$^\circ C/W$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$			1 5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 16\text{V}$			10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	1	1.32	1.8	V
$I_{D(ON)}$	On state drain current	$V_{GS}=10\text{V}$, $V_{DS}=5\text{V}$	30			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}$, $I_D=4.2\text{A}$ $T_J=125^{\circ}\text{C}$		43 58	52 74	$\text{m}\Omega$
		$V_{GS}=4.5\text{V}$, $I_D=2\text{A}$		59	75	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}$, $I_D=4.2\text{A}$		8.5		S
V_{SD}	Diode Forward Voltage	$I_S=1\text{A}$, $V_{GS}=0\text{V}$		0.77	1	V
I_S	Maximum Body-Diode Continuous Current				1.8	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=15\text{V}$, $f=1\text{MHz}$		269	340	pF
C_{oss}	Output Capacitance			65		pF
C_{rss}	Reverse Transfer Capacitance			41		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		1	1.5	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $I_D=4.2\text{A}$		5.7	7.2	nC
$Q_g(4.5\text{V})$	Total Gate Charge			3		nC
Q_{gs}	Gate Source Charge			1.37		nC
Q_{gd}	Gate Drain Charge			0.65		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=10\text{V}$, $V_{DS}=15\text{V}$, $R_L=3.6\Omega$, $R_{GEN}=3\Omega$		2.6	3.8	ns
t_r	Turn-On Rise Time			5.5	8	ns
$t_{D(off)}$	Turn-Off DelayTime			15.2	23	ns
t_f	Turn-Off Fall Time			3.7	5.5	ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=4.2\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		15.5	21	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=4.2\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		7.1		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

F: The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

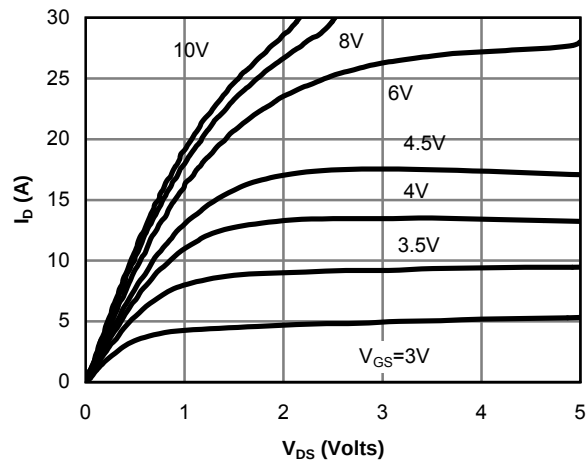


Fig 1: On-Region Characteristics

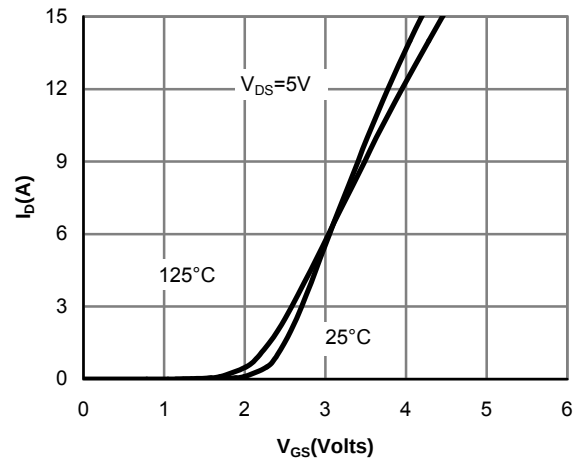


Figure 2: Transfer Characteristics

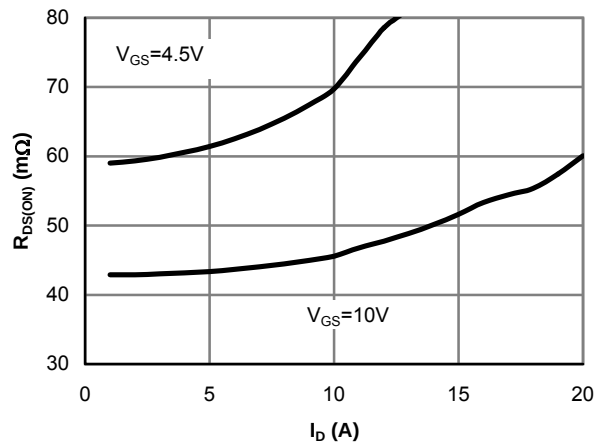


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

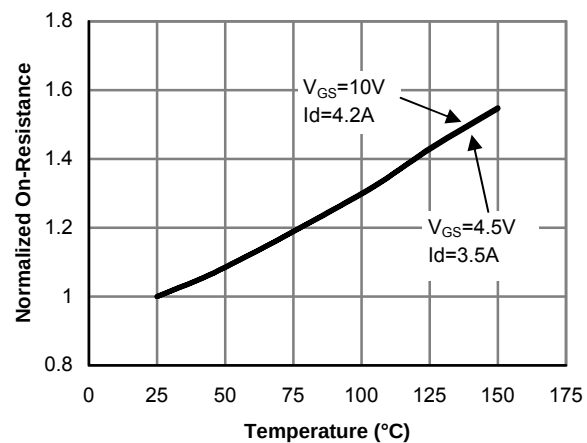


Figure 4: On-Resistance vs. Junction Temperature

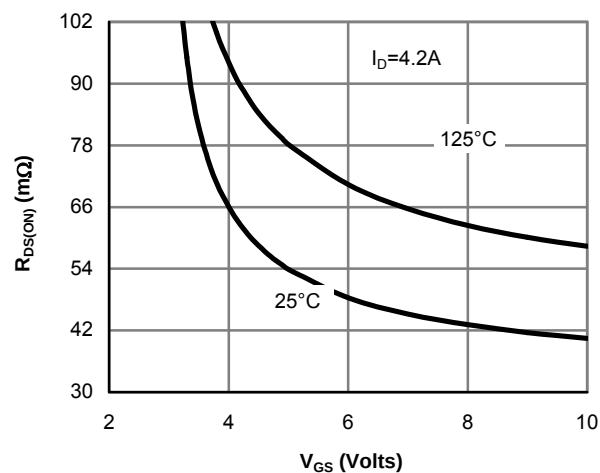


Figure 5: On-Resistance vs. Gate-Source Voltage

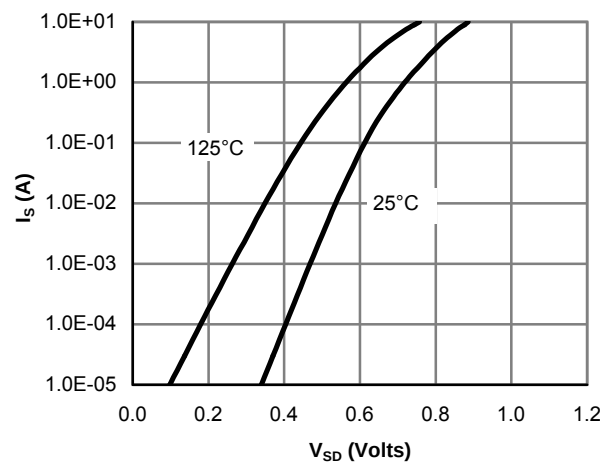


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

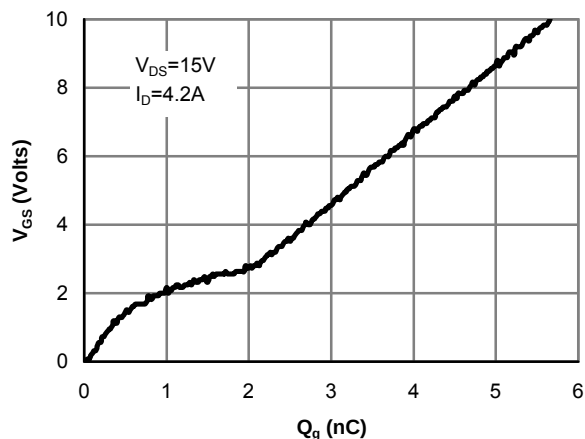


Figure 7: Gate-Charge Characteristics

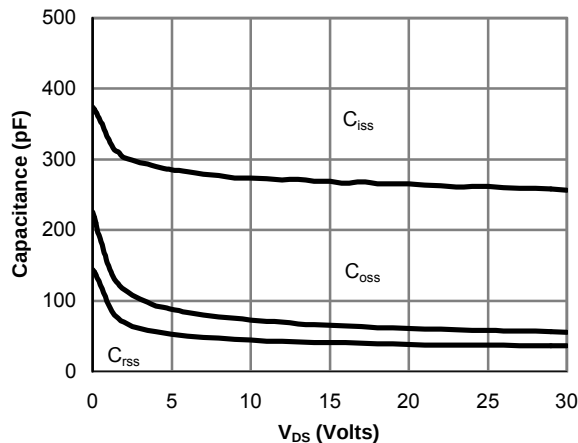


Figure 8: Capacitance Characteristics

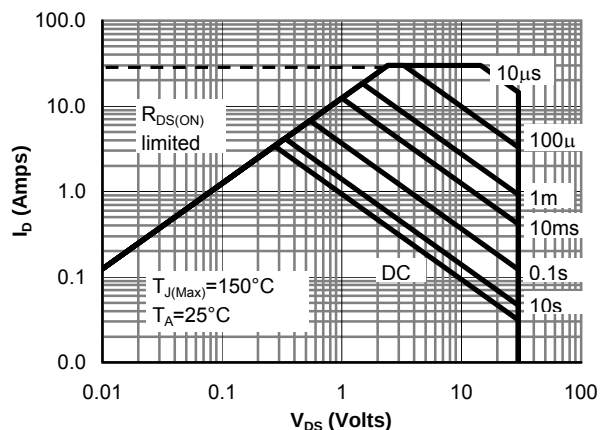


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

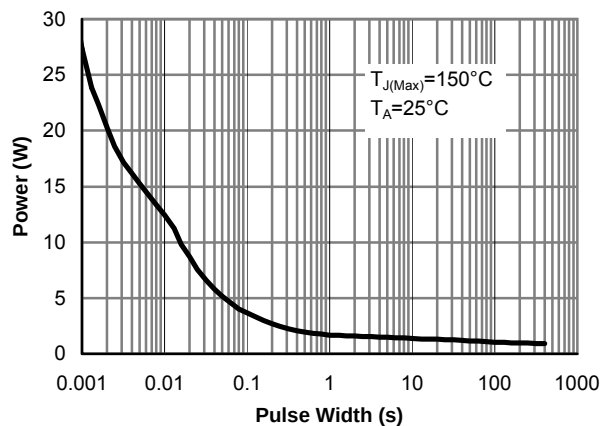


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

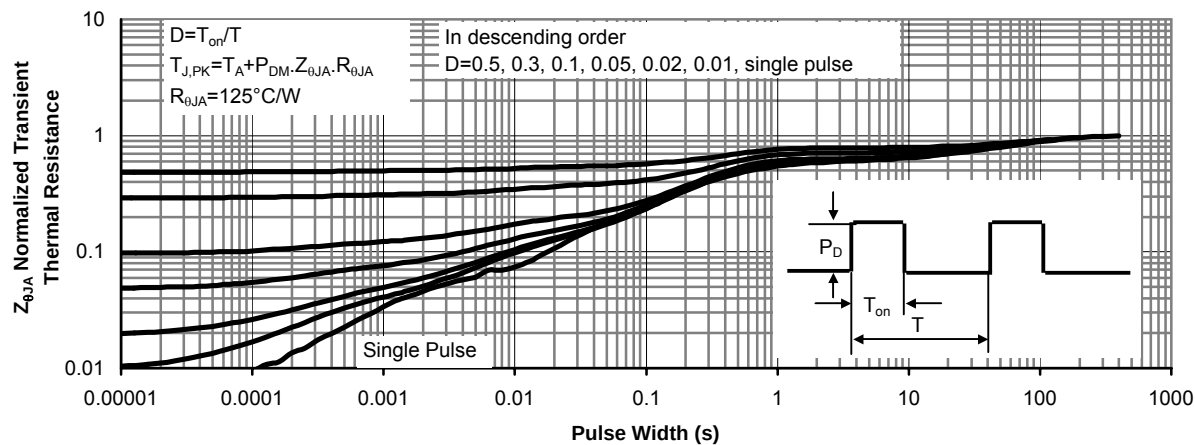


Figure 11: Normalized Maximum Transient Thermal Impedance